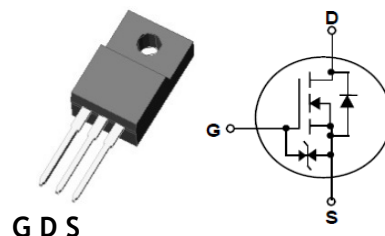


650V N-Channel Super Junction MOSFET

Features

- Very Low FOM ($R_{DS(on)} \times Q_g$)
- Extremely low switching loss
- Built-in ESD Diode
- 100% avalanche tested
- Halogen free and RoHS compliant device

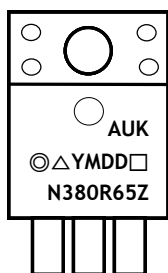


Ordering Information

Part Number	Marking	Package
SJMN380R65ZF	N380R65Z	TO-220F-3L

TO-220F-3L

Marking Information



Column 1: Manufacturer Logo
Column 2: Production Information

- ◎: Management Code
- △: Machine Code
- YMDD: Date Code Marking (Year, Monthly, Daily)
- □: Factory Management Code

Column 3: Device Code

Absolute maximum ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Drain-source voltage	V_{DS}		650	V
Gate-source voltage	V_{GS}		± 20	V
Drain current (DC)	I_D	$T_c=25^\circ\text{C}$	10.4 *	A
		$T_c=100^\circ\text{C}$	6.6 *	A
Drain current (Pulsed) ¹⁾	I_{DM}		31.0 *	A
Single pulsed avalanche energy ²⁾	E_{AS}		142	mJ
Repetitive avalanche current	I_{AR}		1.75	A
Power dissipation	P_D		30	W
Diode dv/dt ruggedness, $V_{DS}=0\ldots 400\text{V}$	dv/dt		15	V/ns
MOSFET dv/dt ruggedness, $V_{DS}=0\ldots 400\text{V}$	dv/dt		50	V/ns
Gate source ESD (Human Body Model)	$V_{ESD(G-S)}$		2000	V
Storage temperature range	T_{stg}		-55~150	$^\circ\text{C}$

* Drain current limited by maximum junction temperature

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 4.17	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=1\text{mA}$, $V_{GS}=0$	650	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=370\mu\text{A}$, $V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=650\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=650\text{V}$, $T_J=150^{\circ}\text{C}$	-	-	100	μA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 1	μA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=3.4\text{A}$	-	0.34	0.38	Ω
	R_g	$f=1\text{MHz}$, Open drain	-	4.7	-	Ω
Input capacitance	C_{iss}	$V_{DS}=200\text{V}$, $V_{GS}=0\text{V}$, $f=1\text{MHz}$	-	1030	-	pF
Output capacitance	C_{oss}		-	27	-	
Reverse transfer capacitance	C_{rss}		-	0.7	-	
Turn-on delay time (Note 3,4)	$t_{d(on)}$	$V_{DD}=325\text{V}$, $I_D=4.8\text{A}$, $R_G=25\Omega$	-	41	-	ns
Rise time (Note 3,4)	t_r		-	34	-	
Turn-off delay time (Note 3,4)	$t_{d(off)}$		-	96	-	
Fall time (Note 3,4)	t_f		-	37	-	
Total gate charge (Note 3,4)	Q_g	$V_{DS}=520\text{V}$, $V_{GS}=10\text{V}$, $I_D=4.8\text{A}$	-	30	-	nC
Gate-source charge (Note 3,4)	Q_{gs}		-	8	-	
Gate-drain charge (Note 3,4)	Q_{gd}		-	10	-	

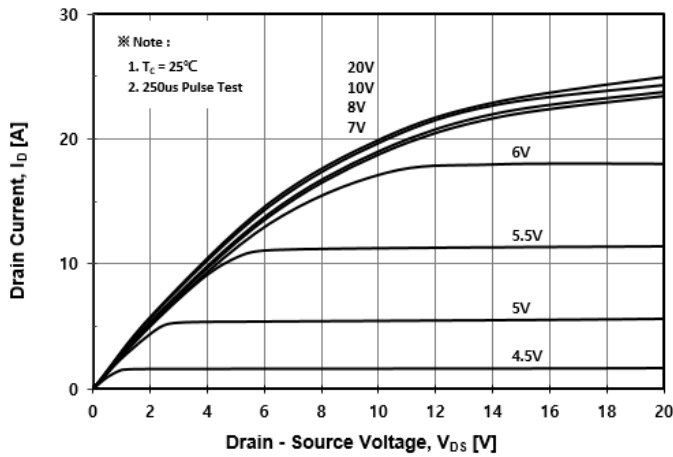
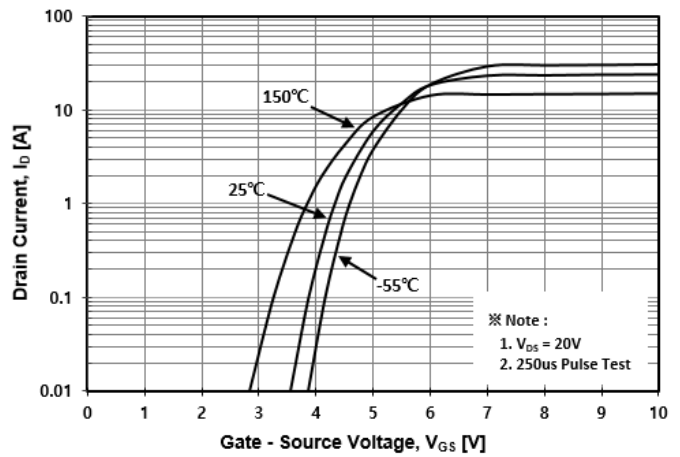
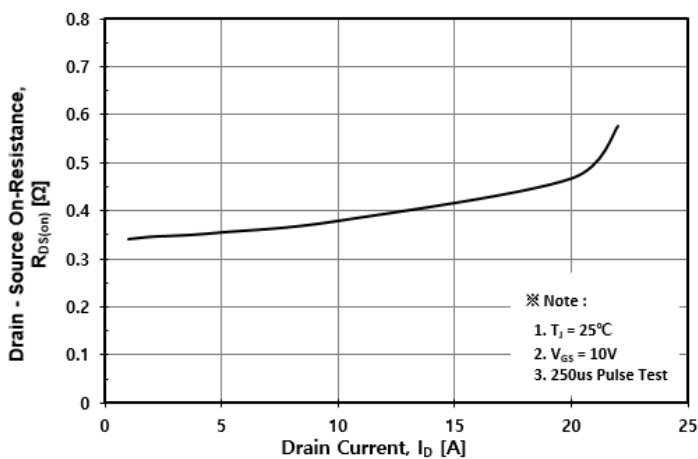
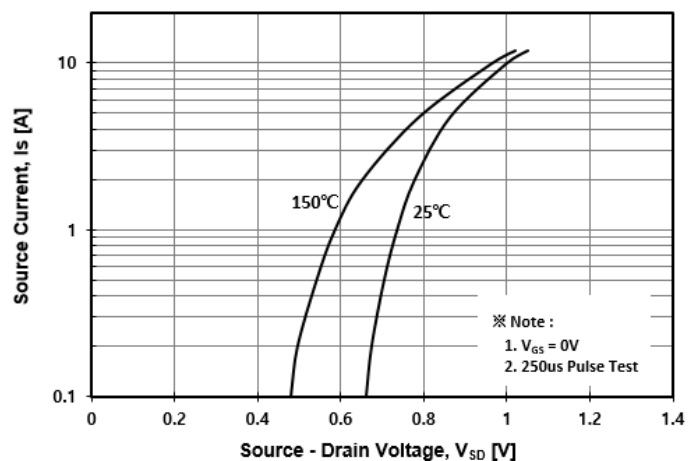
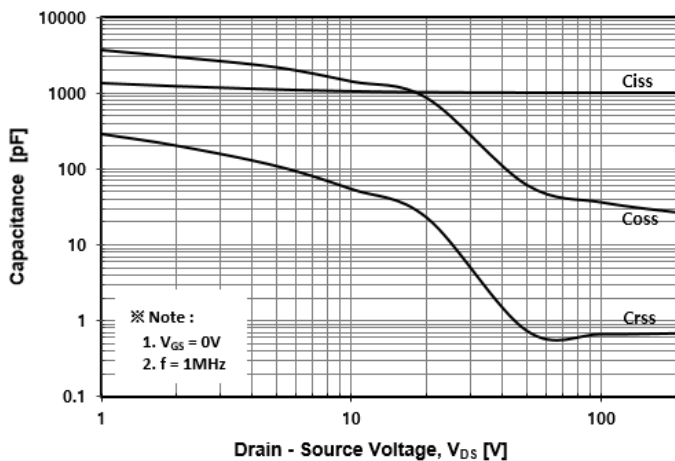
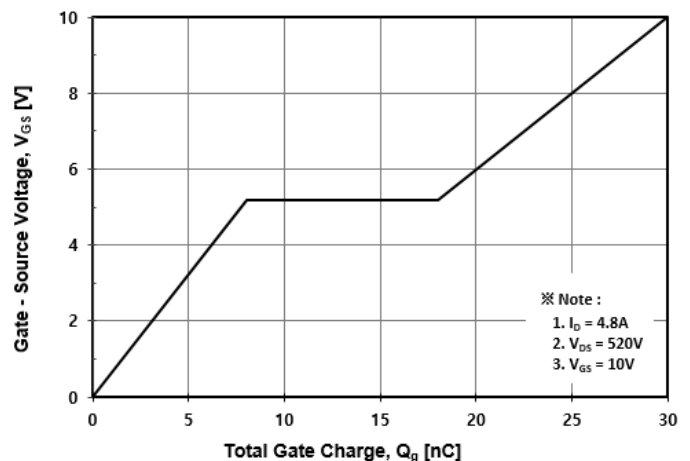
Source-Drain Diode Ratings and Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	10.4	A
Source current (Pulsed)	I_{SM}		-	-	31	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}$, $I_S=4.8\text{A}$	-	-	1.3	V
Reverse recovery time	t_{rr}	$I_S=4.8\text{A}$, $V_{GS}=0\text{V}$ $dI_F/dt=-100\text{A}/\mu\text{s}$	-	285	-	ns
Reverse recovery charge	Q_{rr}		-	2.7	-	μC

Note:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $I_{AS}=1.75\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
4. Essentially Independent of Operating Temperature

Typical Characteristics Curve

Fig. 1 $I_D - V_{DS}$ Fig. 2 $I_D - V_{GS}$ Fig. 3 $R_{DS(ON)} - I_D$ Fig. 4 $I_S - V_{SD}$ Fig. 5 Capacitance - V_{DS} Fig. 6 $V_{GS} - Q_g$ 

Typical Characteristics Curve (Continue)

Fig. 7 $BV_{DSS} - T_J$

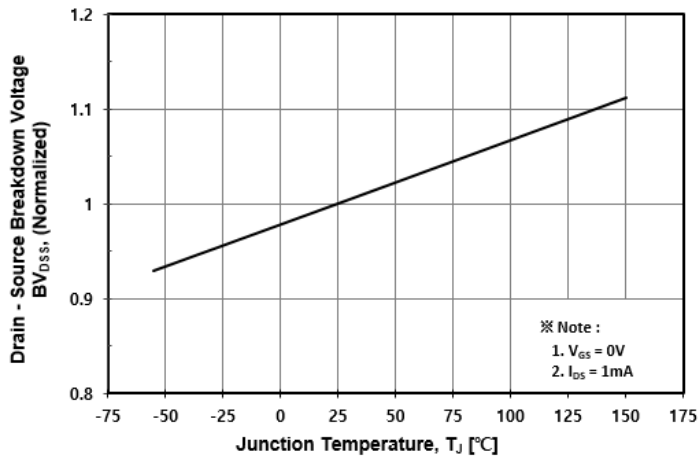


Fig. 8 $R_{DS(ON)} - T_J$

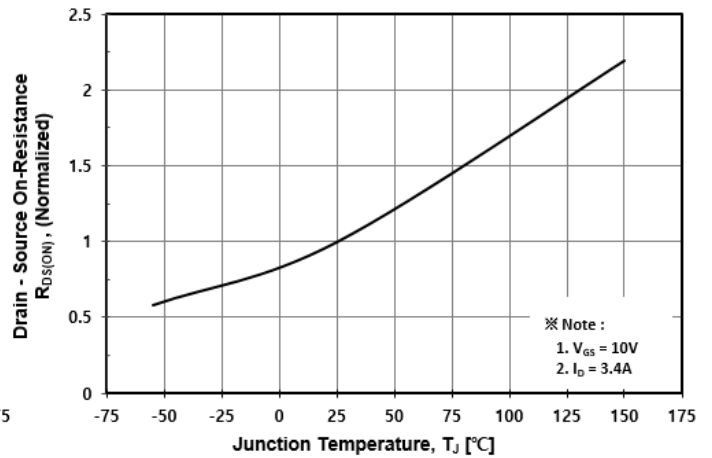


Fig. 9 $I_D - T_C$

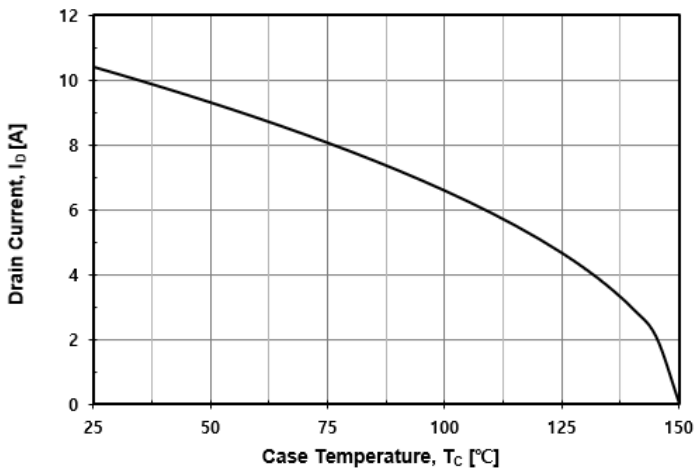


Fig. 10 Safe Operating Area

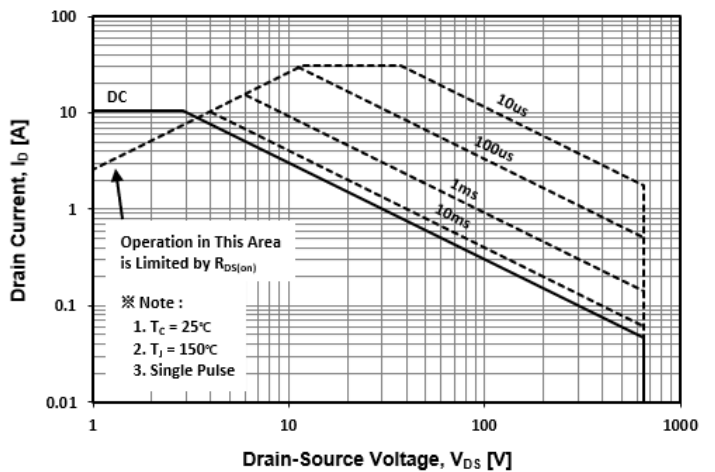


Fig. 11 Transient Thermal Impedance

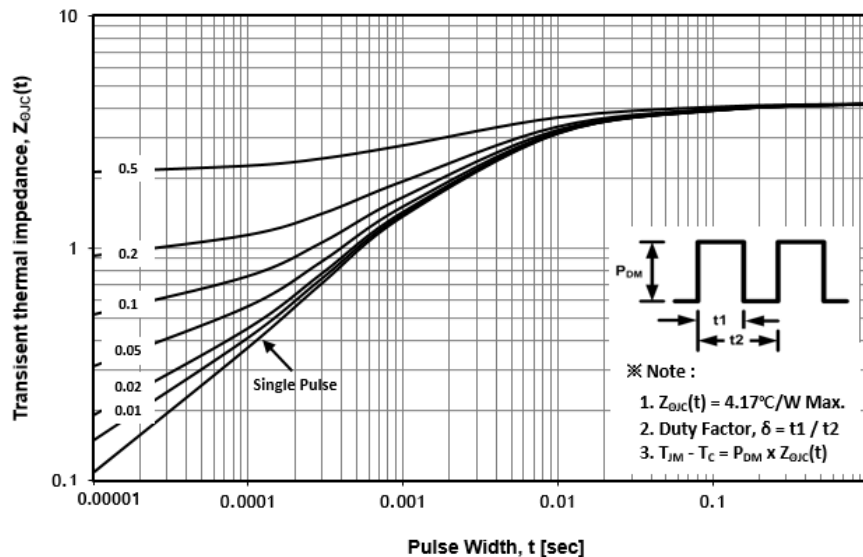


Fig. 12 Gate Charge Test Circuit & Waveform

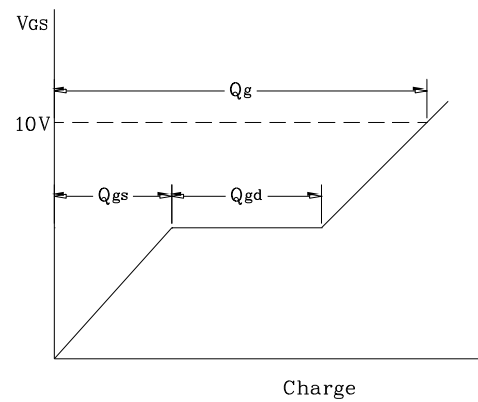
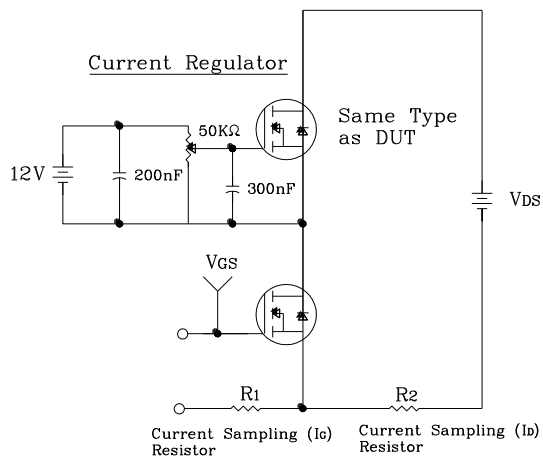


Fig. 13 Resistive Switching Test Circuit & Waveform

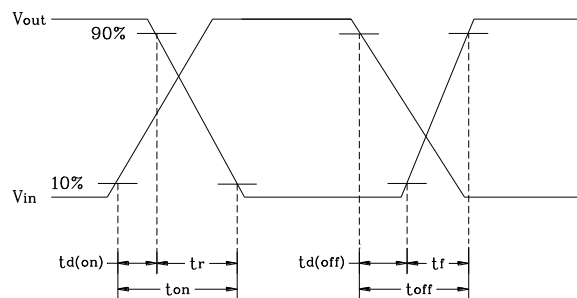
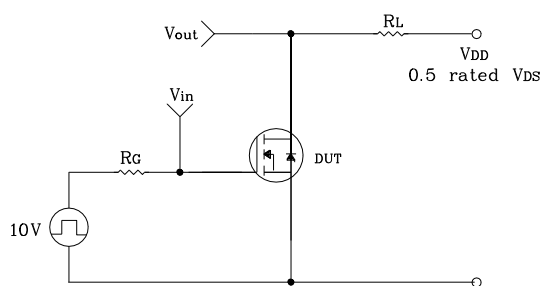


Fig. 14 E_{AS} Test Circuit & Waveform

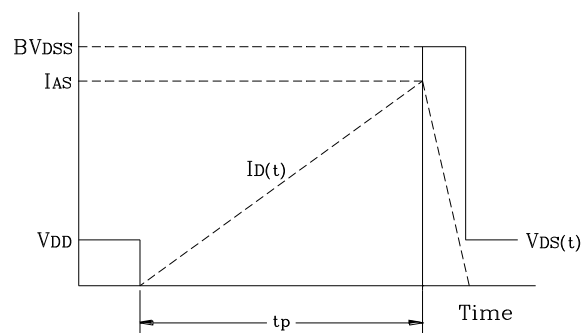
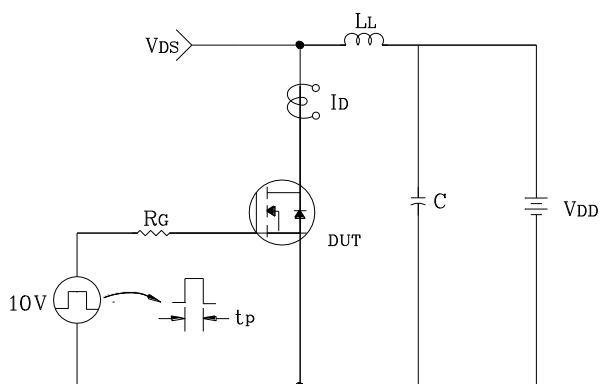
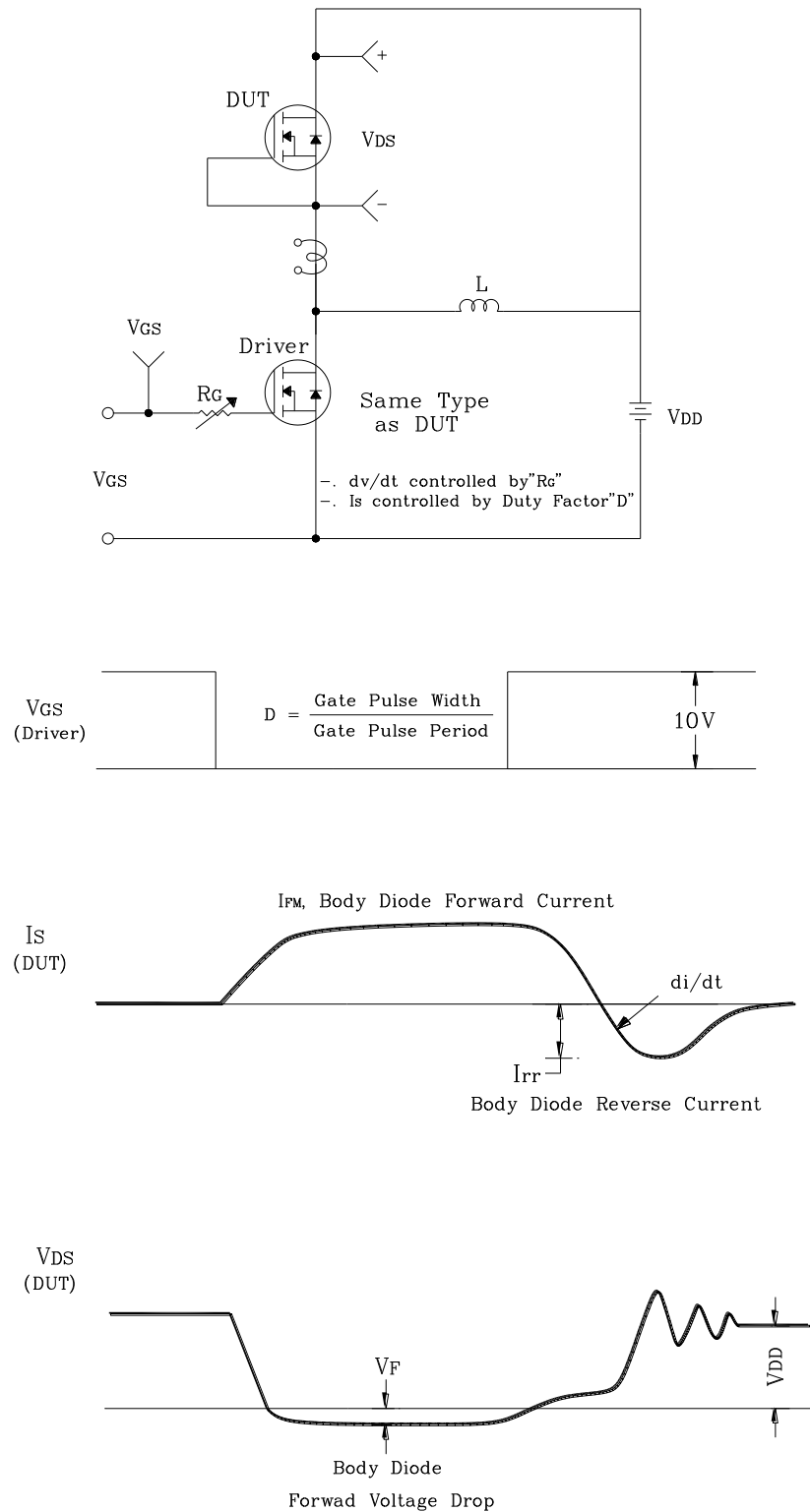
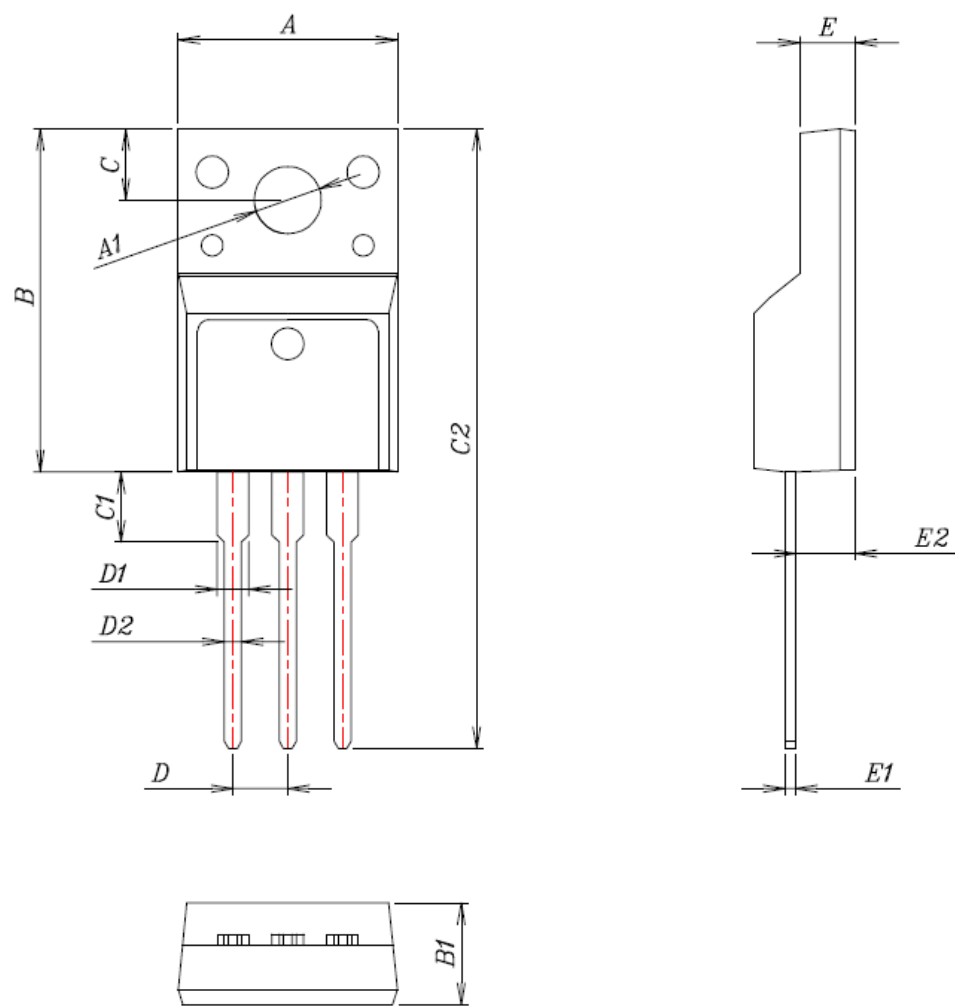


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS
A	10.16±0.30
A1	3.12±0.20
B	15.90±0.50
B1	4.70±0.30
C	3.30±0.25
C1	3.25±0.30
C2	28.70±0.50
D	Typical 2.54
D1	1.47(MAX)
D2	0.80±0.20
E	2.55±0.25
E1	0.50±0.20
E2	2.75±0.30

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